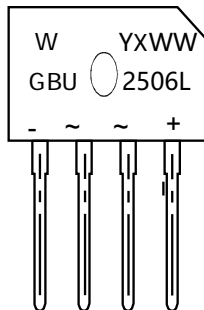


Low VF Bridge Rectifiers



:YUhi fYg

- Glass Passivated Chip Junction
- Low IRRM
- Low VF
- High VRRM

6YbYZ]hg

- Case: GBU
- Terminals: Solderable Per MIL-STD-750
- Reduced power loss and switching transistor

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PIN	DESCRIPTION
1	Input Pin ~
2	Input Pin ~
3	Output Anode +
4	Output Cathode -

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

	Symbols	25	
Maximum Repetitive Peak Reverse Voltage	VRRM	600	V
Maximum RMS voltage	VRMS	420	V
Maximum DC Blocking Voltage	VDC	600	V
Average Rectified Output Current	Io	25	A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	IFSM	300	A
Maximum Forward Voltage at 12.5 A	VF	0.95	V
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	IR	10 500	µA
Typical Junction Capacitance Note1	Cj		pF
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ +150	°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.

2. Mounted on glass epoxy PC board with 4 × 1.5 Å1.5' (3.81 × 3.81 cm) copper pad

RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)

If, Average Forward Current (A)

75 100
Tc, Case Temp (°C)

Current Derating, Case

Capacitance (pF)

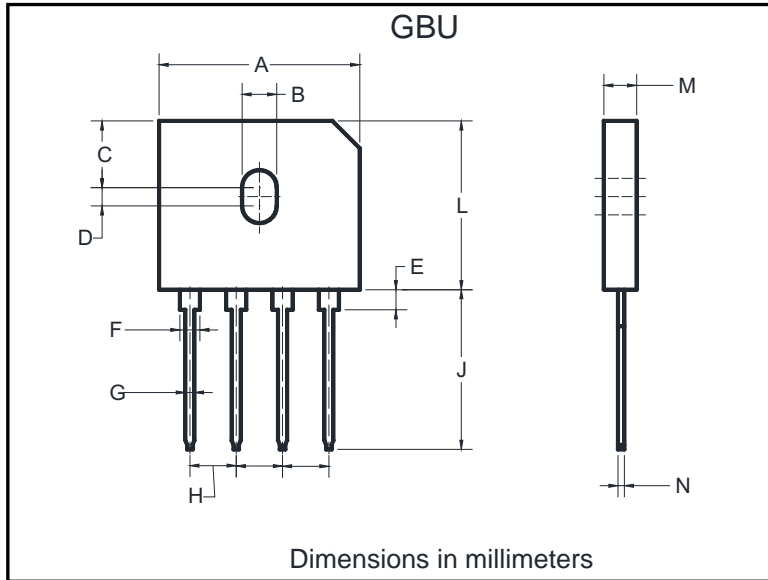
Reverse Voltage (V)

Typical Junction Capacitance

50

VR, Reverse Voltage (Volts)

Typical Reverse Current



GBU		
Dim	Min	Max
A	21.70	22.50
B	3.40	4.10
C	7.40	8.00
D	1.65	2.26
E	2.25	2.85
F	2.05	2.4
G	1.02	1.37
H	4.83	5.43
J	17.0	18.6
L	18.3	18.9
M	3.30	3.66
N	0.46	0.66

